

Features

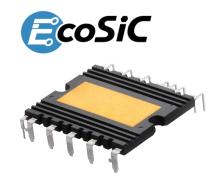
- · HSDIP20 package
- with the 4th Generation SiC-MOSFET
- $\cdot V_{\text{DSS}} = 750 V$
- Low R_{DS(on)}
- · High-speed switching possible
- · Low switching losses
- Tvjmax = 175°C
- · Compact design
- · With high thermal conductivity isolation
- Integrated NTC temperature sensor
- · 4.2kV AC 1s insulation

Construction

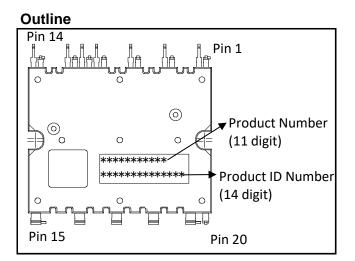
The power module is a 6in1 module. which implements SiC-MOSFETs.

Application

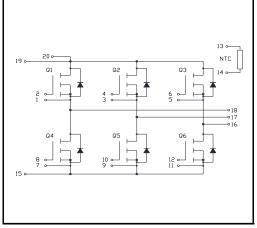
- Automotive application
- · Inverter, Converter
- · (Hybrid) electrical vehicles EV/HEV



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Circuit diagram



Pin No.	Pin Name	Function
1	S1	MOSFET Source
2	G1	MOSFET Gate
3	S2	MOSFET Source
4	G2	MOSFET Gate
5	S3	MOSFET Source
6	G3	MOSFET Gate
7	S4	MOSFET Source
8	G4	MOSFET Gate
9	S5	MOSFET Source
10	G5	MOSFET Gate

Pin No.	Pin Name	Function
11	S6	MOSFET Source
12	G6	MOSFET Gate
13	T1	Thermistor
14	T2	Thermistor
15	Ν	Negative power
16	W	Output
17	V	Output
18	U	Output
19	Р	Positive Power
20	Ps	Positive Power sense

Parameter	Symbol	Conditions	Rating	Unit	
Drain - source voltage	V _{DSS}	$V_{GS} = 0V$	750		
Gate - source voltage (DC)	V _{GSS}		-4 to +21	v	
Gate - source voltage (t _{surge} < 300ns)	V _{GSSsurge}		-4 to +23		
Operation of the intervention of the DO		$Tc = 25^{\circ}C, V_{GS} = 18V$	90		
Continuous drain current (DC)	I _D	Tc = 100°C, V _{GS} = 18V	64	1	
Dulaad drain surrant	I _{D,pulse}	Pulse 1ms, Tc = 25°C, V_{GS} = 18V ^{Note 2), 5)}	195	1	
Pulsed drain current		Pulse 1ms, Tc = 100°C, V_{GS} = 18V ^{Note 2), 5)}	138	А	
Continuous source current (DC)	۱ _s	$Tc = 25^{\circ}C, V_{GS} = 18V$	90		
Pulsed source current	I _{S,pulse}	Pulse 1.5 μ s, Tc = 25°C, V _{GS} = 18V ^{Note 2)}	195		
Body diode surge forward current	I _{S,pulse}	Pulse 1.5µs, Tc = 100°C, $V_{GS} = 0V^{Note 2), 4), 5)$	105		
Total power dissipation Note 3), 5)	Ptot	Tc = 25°C	385	W	
Virtual junction temperature	Tvj		-40 to +175	∘C	
Storage temperature	Tstg		-40 to +125		

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Note 1) If the product is used beyond absolute maximum ratings defined in the specifications,

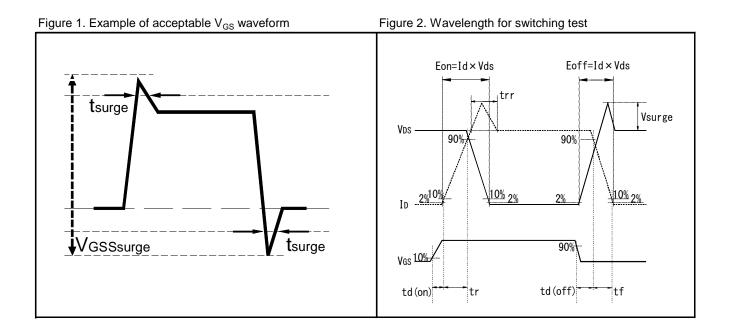
as its internal structure may be damaged, please replace the product with a new one.

Repetition rate should be kept within the range where temperature rise if die should not exceed Tvjmax. Note 2)

Note 3) Case temperature (Tc) is defined on the cooper surface just under the chips.

Note 4) Repetitive pulse, PW≦1.5µs, Duty cycle≦5%

Note 5) Tvj is less than 175°C.





Module (Tvj = 25°C unless otherwise specified)

Deverseter	Currents of	umbel Conditions		Values			
Parameter	Symbol Conditions		Min.	Тур.	Max.	Unit	
Isolation test voltage	V _{isol}	All terminals to baseplate AC 60Hz 1sec.	4200	—	-	V _{rms}	
Stray inductance	L _s	Terminal P to Terminal N	-	46	_	nH	
0		Terminal to heat sink	13.9	_	_		
Creepage distance	—	Terminal to terminal	8.2	_	_	mm	
Clearance distance		Terminal to heat sink	10.2	—	—	~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	
	_	Terminal to terminal	4.3	_	_	mm	
Module flatness (Heatsink side)	_	Measurement point is shown in Figure 3.	0	_	100	μm	
Mounting torque – Mounting to heatsink with M3 screw Note 6)		Mounting to heatsink with M3 screw Note 6)	0.59	0.69	0.78	N∙r	
Terminal pulling strength	_	Load:4.9N(Control terminal), 9.8N(Power terminal) ^{Note 7)}	10	_	_	S	
Terminal bending strength	_	Load:2.45N (Control terminal), 4.9N(Power terminal) ^{Note7)}	2	_	-	tim	
Thermal resistance, junction - case		1 arm heating Note 3)	_	0.28	0.39	°C/\	

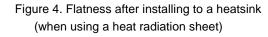
Note 6) 8 mm (outside diameter) plain washers (ISO 7089 to 7094) are recommended.

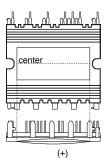
Note 7) EIAJ-ED-4701/400

Note 8) Rth(j-c) was measured after 1chip heating. Heatsink temperature was keep in 25°C. The Rth(j-c) result was calculated from measured structure function, based on JESD51-14 guideline. 100µm thickness of thermally conductive grease was introduced between module and heatsink and fastened with two M4 screws with 0.85N m torque.

Note 9) When installing a module to a heat sink, excessive uneven fastening force might apply stress to inside chips or ceramic of heat sink plate, which will break or crack or degrade a module.
An example of recommended fastening sequence is shown in Figure 5. The temporary fastening torque is set to 20 to 30% of the maximum torque rating.

Figure 3. Measurement point of module flatness





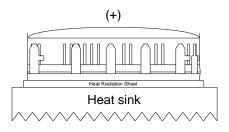


Figure 5. Example of recommended fastening sequence

3/13

2

Temporary fastening: $1 \rightarrow 2$ Permanent fastening: $1 \rightarrow 2$



Deremeter	Symbol	bol Conditions –		Values			Unit	
Parameter	Symbol			Min.	Тур.	Max.	Onit	
		$I_{D} = 58A, V_{GS} = 18V$ $Tvj = 25^{\circ}C$		—	13	—		
Drain - source on resistance	R _{DS(on)}	I _D = 91A, V _{GS} = 18V	Tvj = 25°C	_	14	19	mΩ	
robiotarioo		$I_D = 91A, V_{GS} = 10V$	Tvj = 175°C	_	27	_		
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 750V, V_{GS} = 0V$		_	_	80	μA	
Drain-Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 18.6 mA, T_{vj} = 2$	5°C	750	_	-	V	
Gate - source threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_{D} = 30.8mA^{Note \ 12)}$		2.8	_	4.8	V	
Gate - source leakage current	1	$V_{GS} = +21V, V_{DS} = 0V$		_	—	0.1		
	I _{GSS}	$V_{GS} = -4V, V_{DS} = 0V$			-	_	μA	
Turn - on delay time	t _{d(on)}			Ι	49.3	Ι	ns	
Rise time	t _r	$V_{GS(on)} = 18V, V_{GS(off)} = 0V$	/	-	39.3	-		
Turn - off delay time	t _{d(off)}	V _{DS} = 400V I _D = 90A		-	213.2	-		
Fall time	t _f	$R_{G(on)} = 18\Omega, R_{G(off)} = 18\Omega$)	-	14.2	-		
Turn - on switching loss	E_{on}	Inductive load	-	-	1.61	-	mJ	
Turn - off switching loss	E _{off}			-	1.79	-	mJ	
Input capacitance	C _{iss}	$V_{DS} = 500V, V_{GS} = 0V, 1MH$	Ηz	_	4.58	_	nF	
Total gate charge	Q_g	$V_{GS(on)} = 18V, V_{GS(off)} = 0V$	/	_	170	_		
Gate - source charge	Q_{gs}	$V_{DS} = 500V$		_	39	_	nC	
Gate - drain charge	Q_gd	I _D = 58A			42			
Internal gate resistance	R _{Gint}	Tvj = 25°C		_	1	_	Ω	

MOSFET electrical characteristics (Tvj = 25°C unless otherwise specified)

Note 10) Evenly apply thermally-conductive grease with 100µm to 200µm thickness over the contact surface between the module and the heat sink. Pay attention not to have any dirt left on the contact surface between the module and the heat sink.

It is recommended to install a module directly to a heat sink after applying grease.

Note 11) When installing a module to a heat sink, inserting a heat radiation sheet between a module and a heat sink might apply stress depending on thickness and elastic modulus of the sheet to inside chips or ceramic of heat sink plate, which will break or crack or degrade a module.
When using a heat radiation sheet, it is needed to prevent power module from bending into + side of Figure 4.

- Note 12) Tested after applying $V_{GS} = 21V$ for 100ms.
- Note 13) SiC devices have lower short circuit withstand capability due to high current density. Please be advised to pay careful attention to short circuit accident and try to adjust protection time to shutdown them as short as possible.



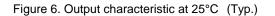
Parameter	Symbol	Conditions			Values		Unit
Falameter	Symbol			Min.	Тур.	Max.	Unit
	V _{SD}	$V_{ce} = 0V$. $I_e = 91A$	Tvj = 25°C	-	3.9	—	
Souce - drain			Tvj = 175°C	1	4.0	-	
voltage		$V_{GS} = 18V, I_{S} = 91A$	Tvj = 25°C	—	1.15	—	v
		$v_{GS} = 10^{\circ}, 1_{S} = 31A$	Tvj = 175°C	—	2.03	-	

Body diode electrical characteristics (Tvj = 25°C unless otherwise specified)

NTC Thermistor electrical characteristics (Tvj = 25°C unless otherwise specified)

Parameter	Symbol Conditions	Conditions	Values			Unit	
Falameter	Symbol	Conditions	Min.	Тур.	Max.	Onit	
NTC rated resistance	R ₂₅	Tc = 25°C	-	10	-	kΩ	
NTC B Value	B _{50/25}			3380		К	
Maximum operating current	_			-	0.1	mA	





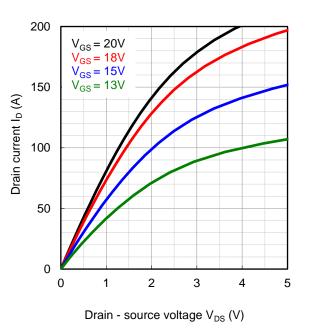


Figure 7. Drain - source voltage characteristic (Typ.)

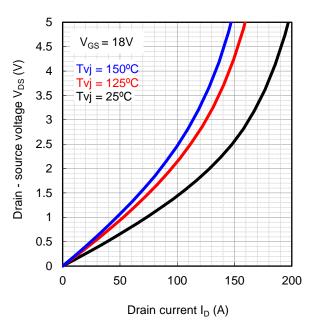
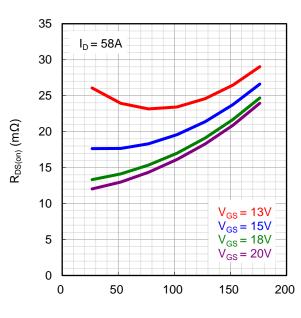


Figure 8. Drain - source voltage characteristic at 25°C (Typ.) 5 $I_{\rm D} = 130 {\rm A}$ $I_{\rm D} = 90A$ $I_{D} = 50A$ 4 Drain - source voltage V_{DS} (V) $I_{\rm D} = 20A$ 3 2 1 0 12 14 16 18 20

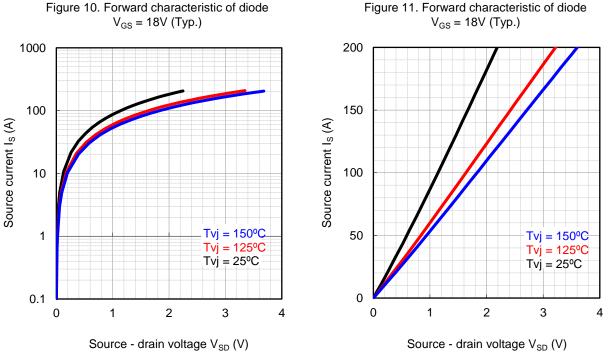
Gate - source voltage $V_{\text{GS}}\left(V\right)$



Figure 9. R_{DS(on)} vs. Tvj characteristic (Typ.)



Virtual junction temperature Tvj (°C)





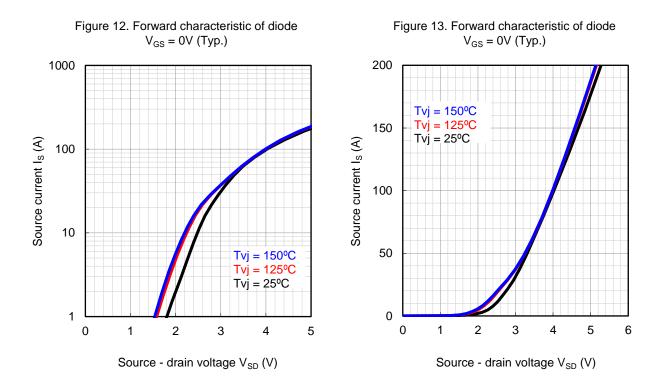
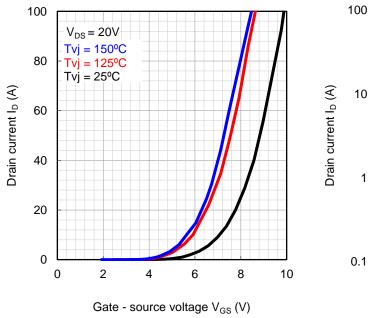
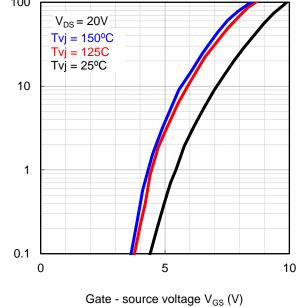


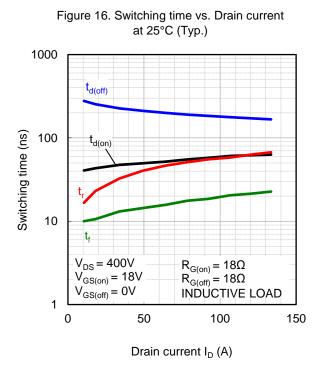
Figure 14. Drain current vs. Gate - source voltage (Typ.)

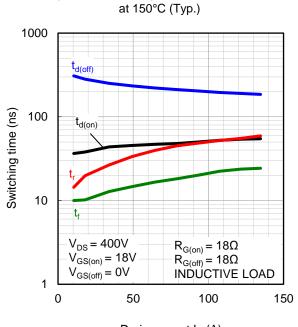
Figure 15. Drain current vs. Gate - source voltage (Typ.)

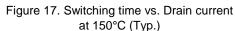


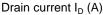












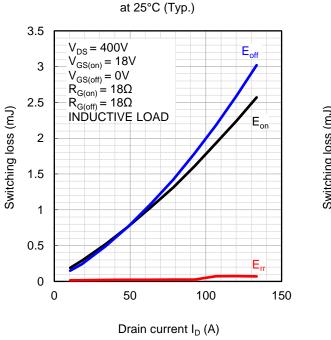
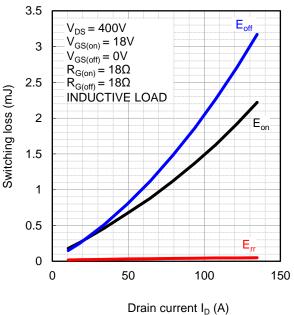


Figure 18. Switching loss vs. Drain current

Figure 19. Switching loss vs. Drain current at 150°C (Typ.)





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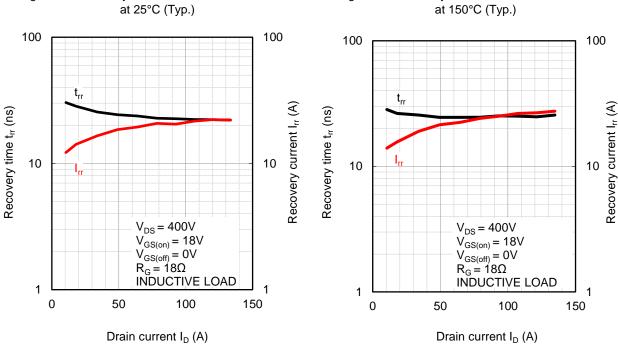


Figure 20. Recovery characteristic vs. Drain current at 25°C (Typ.)

Figure 22. Switching time vs. Gate resistance at 25°C (Typ.)

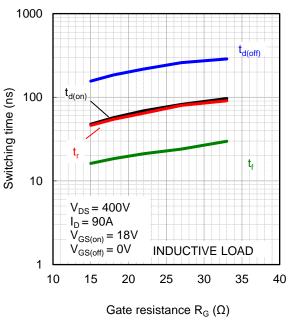
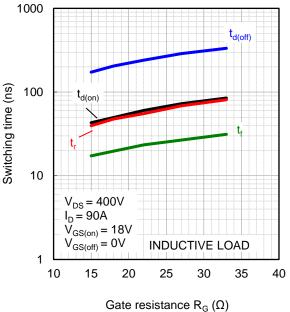


Figure 23. Switching time vs. Gate resistance at 150°C (Typ.)

Figure 21. Recovery characteristic vs. Drain current





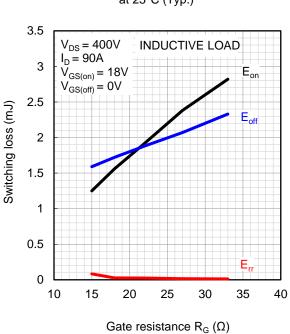


Figure 24. Switching loss vs. Gate resistance at 25°C (Typ.)

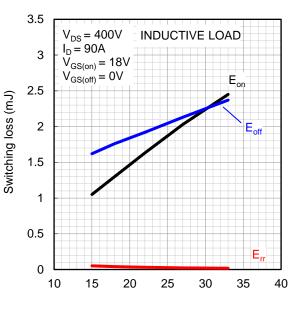
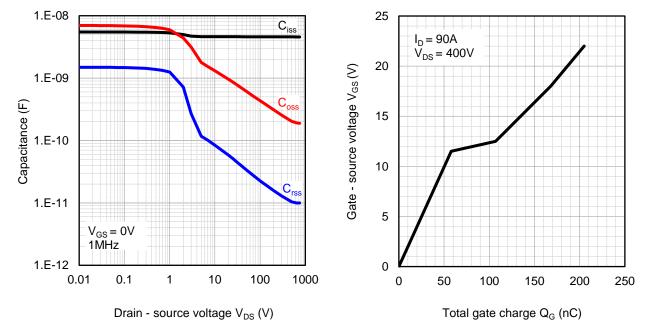


Figure 25. Switching loss vs. Gate resistance at 150°C (Typ.)

Gate	resistance	R_{G}	(Ω)
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Figure 26. Capacitance vs. Drain - source voltage at 25°C (Typ.)

Figure 27. Gate charge characteristic at 25°C (Typ.)



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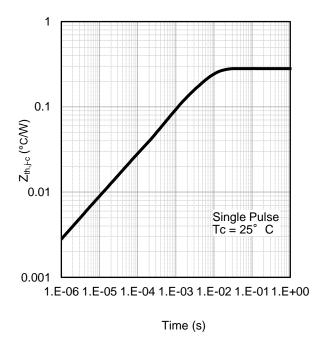
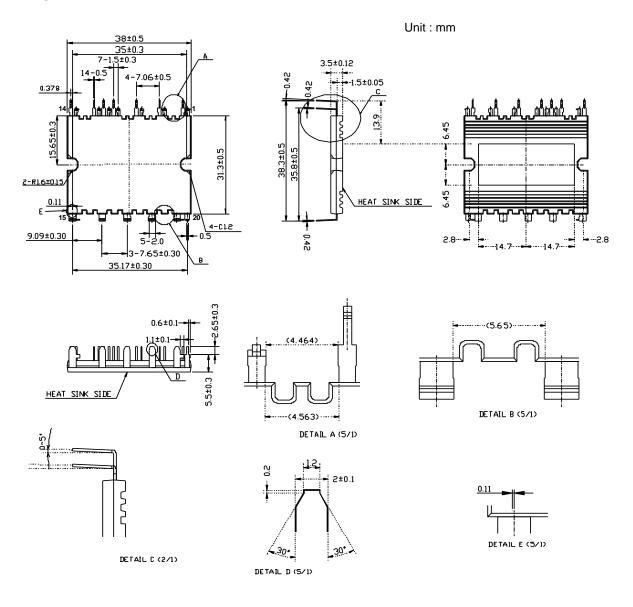


Figure 28. Transient thermal impedance (Typ.)



Package outlines





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